

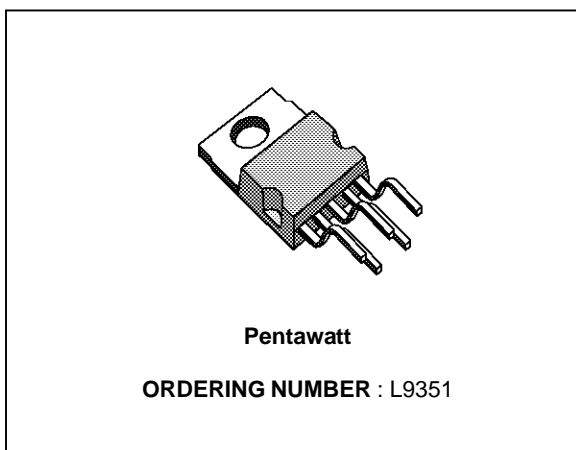
## HIGH SIDE DRIVER

ADVANCE DATA

- LOW SATURATION VOLTAGE
- TTL COMPATIBLE INPUT
- WIDE SUPPLY VOLTAGE
- VERY LOW QUIESCENT CURRENT (30mA max)
- NO EXTERNAL COMPONENTS
- INTERNAL RECIRCULATION PATH FOR FAST DECAY OF INDUCTIVE LOAD CURRENT
- SHORT CIRCUIT PROTECTION
- FAILSAFE OPERATION : OUTPUT IS OFF IF THE LOGIC INPUT IS LEFT OPEN

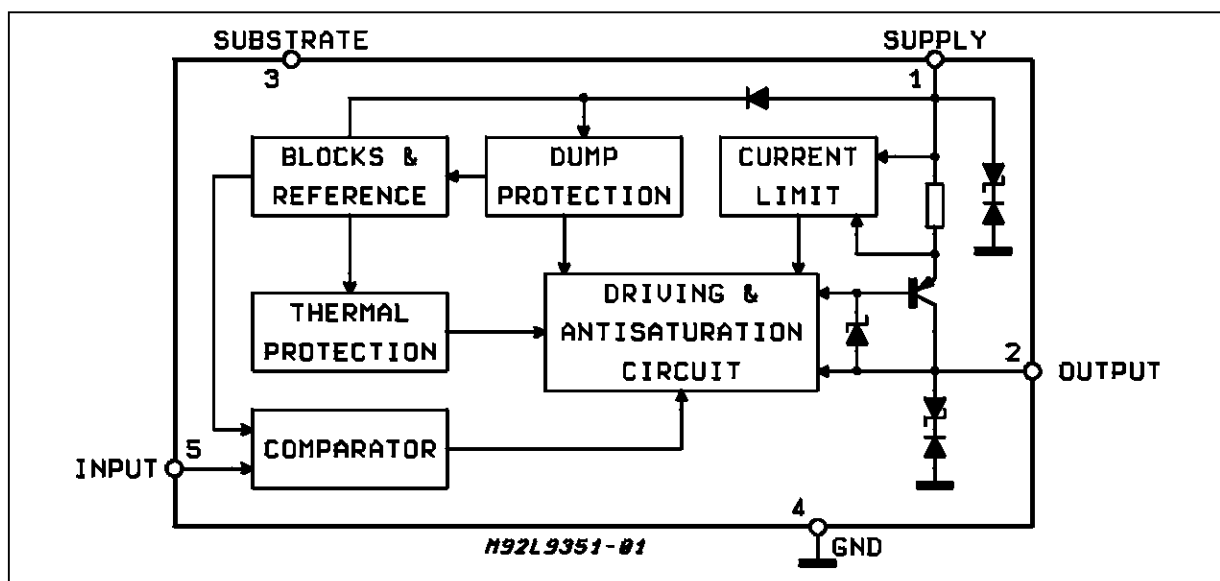
### DESCRIPTION

The L9351 is a monolithic integrated circuit designed to drive grounded resistive, inductive or mixed loads from the power supply positive side. Very low standby current (30mA max.) and internally implemented protections against load dump and reverse voltages make the device very useful in automotive applications. No external components are required because the output recirculation clamping zener is included in the chip. This zener can withstand a recirculation peak current of 550mA on a 80mH/25Ω load.



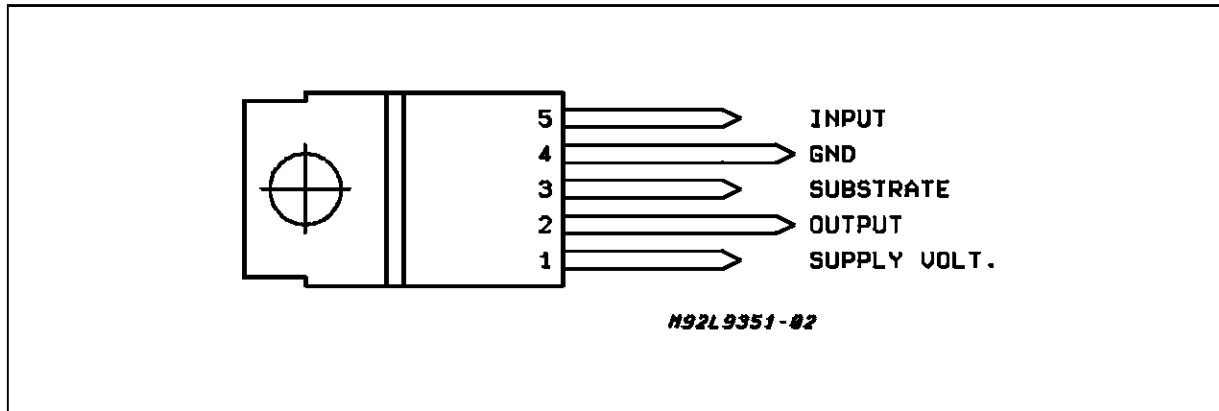
The device is self-protected against overtemperature, overvoltage and overcurrent conditions. The L9351 operates over the full battery voltage range, from 4.5V (cold cranking) up to 24V (jump starting). The L9351 withstands reverse battery conditions (-13V) and supply voltage transients up to 80V limiting the maximum output transistor  $V_{EC}$  to 70V by an internal zener. ON and OFF delaytimes of 25μs max in any output status, including recirculating situation, allow PWM use of L9351.

### BLOCK DIAGRAM



## L9351

### PIN CONNECTION (top view)



**Note :** Pin 3 must be left open or connected to ground.

### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_s$	D.C. Supply Voltage	24	V
	D.C. Reverse Supply Voltage	-13	V
	Load Dump: $5\text{ms} \leq t_{\text{rise}} \leq 10\text{ms}$ $t_f$ Fall Time Constant = 100ms, $R_{\text{source}} \geq 0.5\Omega$	60	V
	Low Energy Spikes: $R_{\text{source}} \geq 10\Omega$ , $t_{\text{rise}} = 1\mu\text{s}$ , $t_f = 2\text{ms}$ , $f_r$ Repetition Frequency = 0.2Hz	$\pm 85$	V
$V_i$	Input Voltage	-0.3 to 7	V
$I_o$	Output Current	Internally Limited	
$P_{\text{tot}}$	Total Power Dissipation at $T_{\text{case}} = 90^\circ\text{C}$	17.1	W
$T_j, T_{\text{stg}}$	Junction and Storage Temperature	-55 to 150	$^\circ\text{C}$

### THERMAL DATA

Symbol	Parameter	Value	Unit
$R_{\text{th j-amb}}$	Thermal Resistance Junction-ambient	Max. 80	$^\circ\text{C}/\text{W}$
$R_{\text{th j-case}}$	Thermal Resistance Junction-case	Max. 3.5	$^\circ\text{C}/\text{W}$

**ELECTRICAL CHARACTERISTICS**

( $V_S = 14.4V$ ,  $-40^{\circ}C \leq T_j \leq +125^{\circ}C$  unless otherwise specified).

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_S$	Operating Supply Voltage		4.5		24	V
$V_{IH}$	Input Voltage High	$4.5 < V_S < 24$	2.0			V
$V_{IL}$	Input Voltage Low			1	0.8	V
$I_I$	Input Current	$0.8 < V_I < 5.5V$			40	$\mu A$
$I_{PL}$	Output Leakage Current	$V_O = 0V$ $V_S = 24V$ $V_I < 0.8V$			140	$\mu A$
$V_{sat}$	Output Saturation Voltage	$I_O = 125mA$ $V_S = 4.5V$			0.5	V
		$I_O = 225mA$ $V_S = 14.4V$			0.5	V
		$I_O = 550mA$ $V_S = 14.4V$			0.7	V
$I_{SC}$	Output Short Circuit Current		0.6	1.5		A
$I_Q$	Quiescent Current	$V_I > 2V$			30	mA
		$V_I < 0.8V$ Stand-by Condition		100	150	$\mu A$
$V_{ZO}$	Negative Output Zener Voltage	$R_L = 25\Omega$ $L = 80mH$ on $V_I$ Transition from "1" to "0"	-36	-30	-24	V
$T_{on}$	Turn ON Delay	Resistive Load $R_L = 25\Omega$ , $T_j = 25^{\circ}C$ (fig.2)			20	$\mu s$
$T_{off}$	Turn OFF Delay				25	$\mu s$

Figure 1 : Typical Automotive Application Circuit.

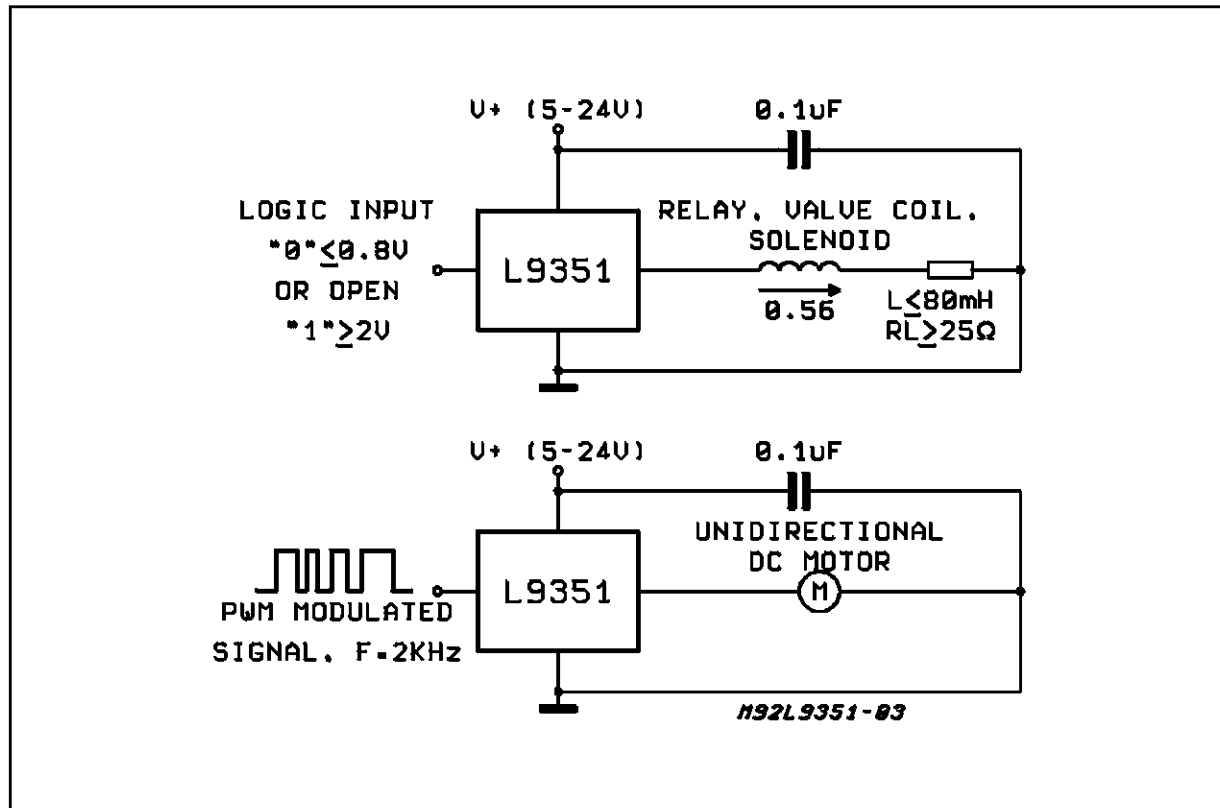


Figure 2 : Resistive Load.

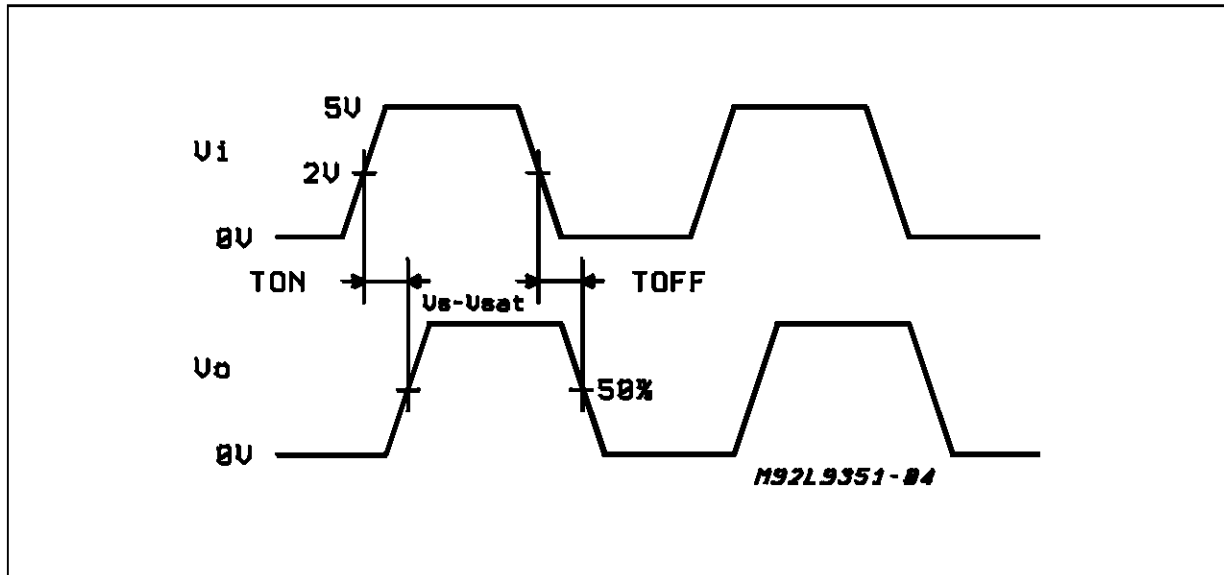
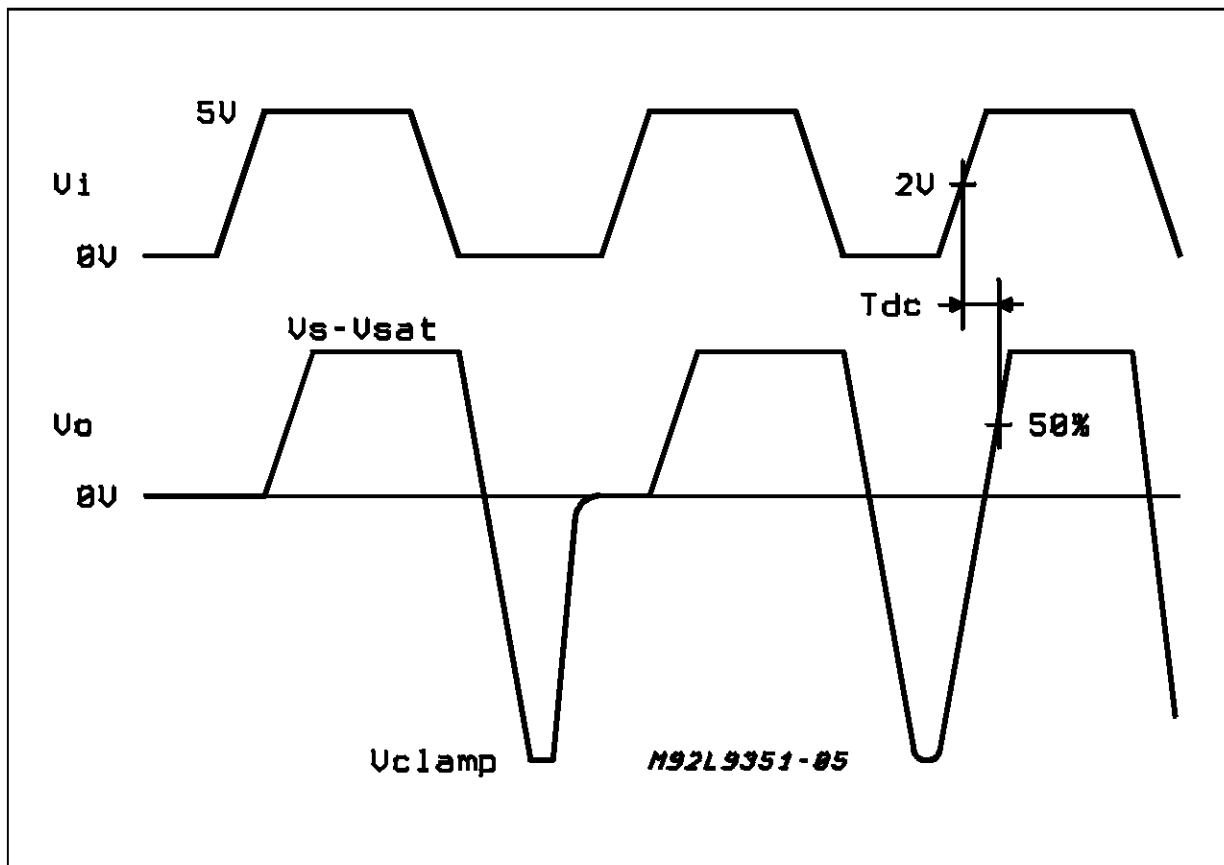
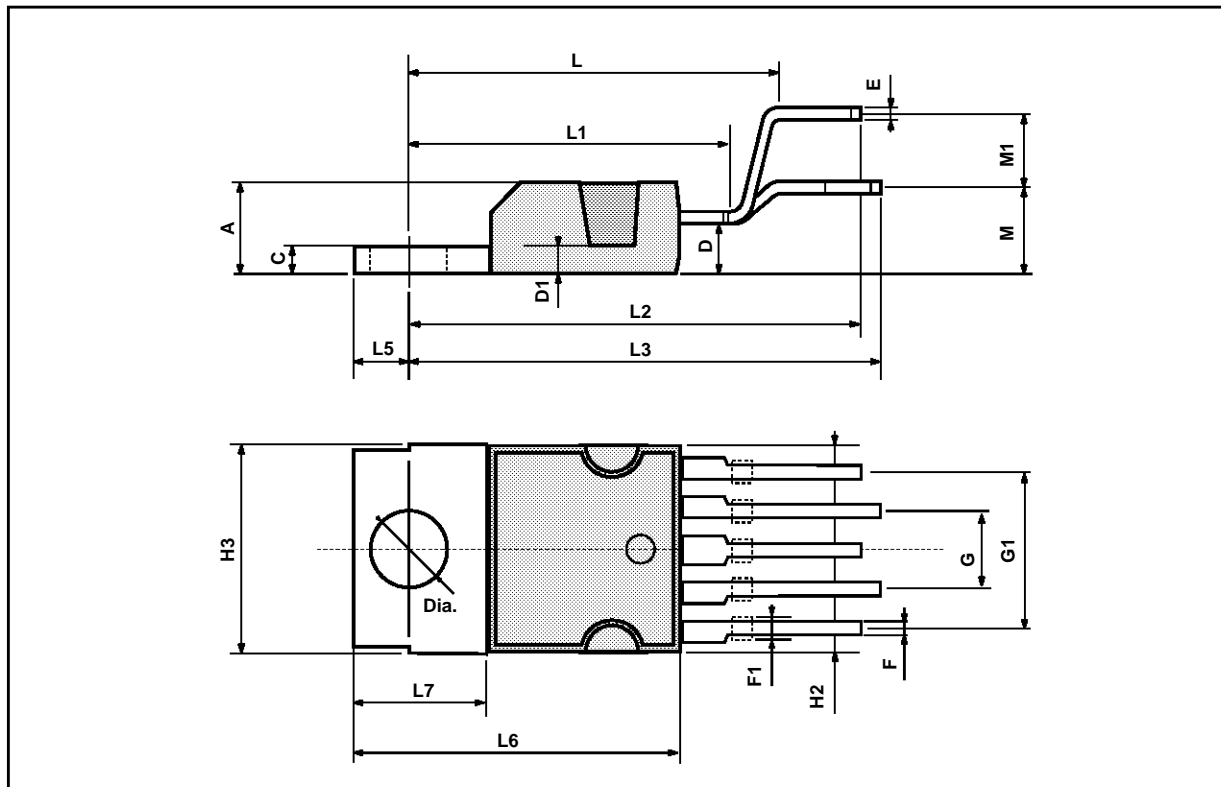


Figure 3 : Inductive Load.



## PENTAWATT PACKAGE MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			4.8			0.189
C			1.37			0.054
D	2.4		2.8	0.094		0.110
D1	1.2		1.35	0.047		0.053
E	0.35		0.55	0.014		0.022
F	0.8		1.05	0.031		0.041
F1	1		1.4	0.039		0.055
G		3.4		0.126	0.134	0.142
G1		6.8		0.260	0.268	0.276
H2			10.4			0.409
H3	10.05		10.4	0.396		0.409
L		17.85			0.703	
L1		15.75			0.620	
L2		21.4			0.843	
L3		22.5			0.886	
L5	2.6		3	0.102		0.118
L6	15.1		15.8	0.594		0.622
L7	6		6.6	0.236		0.260
M		4.5			0.177	
M1		4			0.157	
Dia	3.65		3.85	0.144		0.152



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